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November 2013

SSN1N45B

N-Channel B-FET

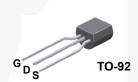
450 V, 0.5 A, 4.25 Ω

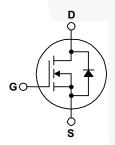
Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar, DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for electronic ballasts based on half bridge configuration.

Features

- 0.5 A, 450 V, $R_{DS(on)}$ = 4.25 Ω @ V_{GS} = 10 V Low Gate Charge (typical 6.5 nC)
- Low Crss (typical 6.5 pF)
- · 100% Avalanche Tested
- · Improved dv/dt Capability
- Gate-Source Voltage ± 50V Guaranteed





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		SSN1N45BTA	Unit
V _{DSS}	Drain-Source Voltage		450	V
I _D	Drain Current - Continuous (T _C = 25°C)		0.5	Α
	- Continuous (T _C = 100°C)		0.32	А
I _{DM}	Drain Current - Pulsed	(Note 1)	4.0	А
V_{GSS}	Gate-Source Voltage		± 50	V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		108	mJ
I _{AR}	Avalanche Current	(Note 1)	0.5	А
E _{AR}	Repetitive Avalanche Energy	(Note 1)	0.25	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		5.5	V/ns
P _D	Power Dissipation (T _A = 25°C)		0.9	W
	Power Dissipation (T _L = 25°C)		2.5	W
	- Derate above 25°C		0.02	W/°C
T _J , T _{stg}	Operating and Storage Temperature Range		-55 to +150	°C
T _L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300	°C

Thermal Characteristics

Symbol	Parameter	SSN1N45BTA	Unit	
$R_{\theta JL}$	Thermal Resistance, Junction-to-Lead, Max.	(Note 5a)	50	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	(Note 5b)	140	°C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
SSN1N45BTA	1N45B	TO-92	AMMO	N/A	N/A	2000 units

Electrical Characteristics T_c = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	450			V
ΔBV_{DSS} / ΔT_{J}	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, Referenced to 25°C		0.5		V/°C
I _{DSS}	Zara Cata Valtaga Drain Current	V _{DS} = 450 V, V _{GS} = 0 V			10	μΑ
	Zero Gate Voltage Drain Current	V _{DS} = 360 V, T _C = 125°C			100	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 50 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -50 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
On Cha	racteristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	2.3	3.0	3.7	V
()		$V_{DS} = V_{GS}, I_{D} = 250 \text{ mA}$	3.5	4.2	4.9	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 0.25 A		3.4	4.25	Ω
9 _{FS}	Forward Transconductance	$V_{DS} = 50 \text{ V}, I_D = 0.25 \text{ A}$	\ 	0.7		S
	ic Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$		185	240	pF
C _{oss}	Output Capacitance	f = 1.0 MHz		29	40	pF
C _{rss}	Reverse Transfer Capacitance			6.5	8.5	pF
Switchi	ing Characteristics					
t _{d(on)}	Turn-On Delay Time	$V_{DD} = 225 \text{ V}, I_D = 0.5 \text{ A},$		7.5	25	ns
t _r	Turn-On Rise Time	$R_{G} = 25 \Omega$		21	50	ns
t _{d(off)}	Turn-Off Delay Time	NG = 20 22		23	55	ns
t _f	Turn-Off Fall Time	(Note 4)	/	36	80	ns
Qg	Total Gate Charge	$V_{DS} = 360 \text{ V}, I_{D} = 0.5 \text{ A},$		6.5	8.5	nC
Q_{gs}	Gate-Source Charge	V _{GS} = 10 V	/	0.9	/	nC
Q _{gd}	Gate-Drain Charge	(Note 4)		3.2		nC
Drain-S	Source Diode Characteristics a	nd Maximum Ratings				
I _S	Maximum Continuous Drain-Source Did			0.5	Α	
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				4.0	Α
		$V_{GS} = 0 \text{ V}, I_{S} = 0.5 \text{ A}$		/	1.4	V
V _{SD}	Drain-Source Diode Forward Voltage	165 = 0 1, 15 = 0.0 / t			1	
V _{SD}	Prain-Source Diode Forward Voltage Reverse Recovery Time	$V_{GS} = 0 \text{ V, } I_S = 0.5 \text{ A,}$		102		ns

Notes:

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. L = 75 mH, I_{AS} = 1.6 A, V_{DD} = 50 V, R_G = 25 Ω, starting T_J = 25°C.

3. I_{SD} ≤ 0.5 A, di/dt ≤ 300 A/μs, V_{DD} ≤ BV_{DSS}, starting T_J = 25°C.

4. Essentially independent of operating temperature.

5. a) Reference point of the R_{θ,JI} is the drain lead.

b) When mounted on 3"x4.5" FR-4 PCB without any pad copper in a still air environment.

(R_{θ,JA} is the sum of the junction-to-case and case-to-ambient thermal resistance. R_{θCA} is determined by the user's board design)

Typical Characteristics

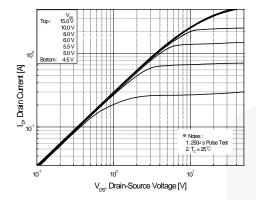


Figure 1. On-Region Characteristics

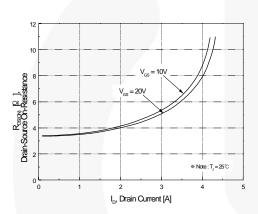


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

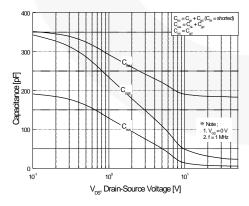


Figure 5. Capacitance Characteristics

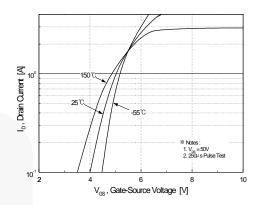


Figure 2. Transfer Characteristics

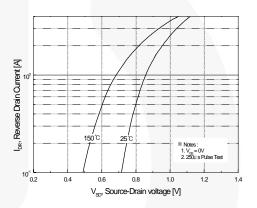


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

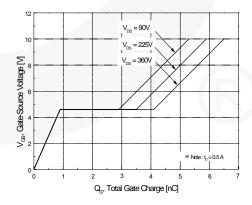


Figure 6. Gate Charge Characteristics

Typical Characteristics (continued)

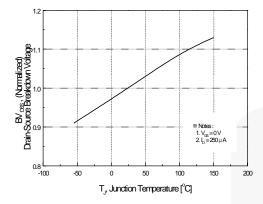


Figure 7. Breakdown Voltage Variation vs. Temperature

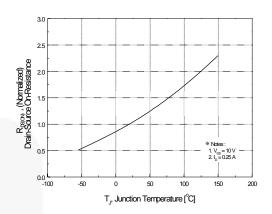


Figure 8. On-Resistance Variation vs. Temperature

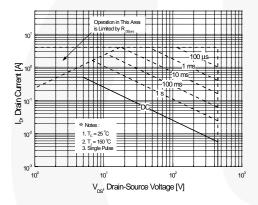


Figure 9. Maximum Safe Operating Area

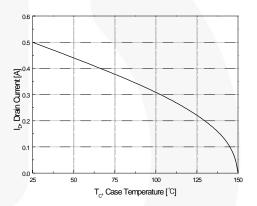


Figure 10. Maximum Drain Current vs. Case Temperature

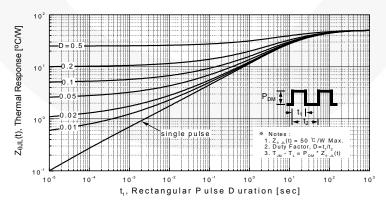


Figure 11. Transient Thermal Response Curve

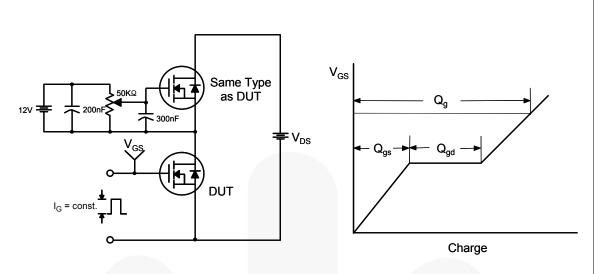


Figure 12. Gate Charge Test Circuit & Waveform

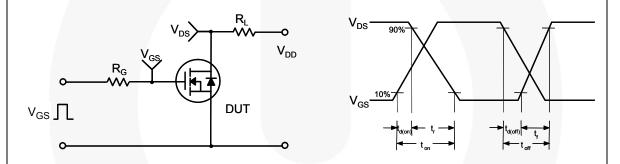


Figure 13. Resistive Switching Test Circuit & Waveforms

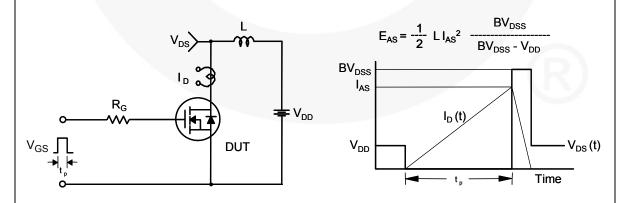
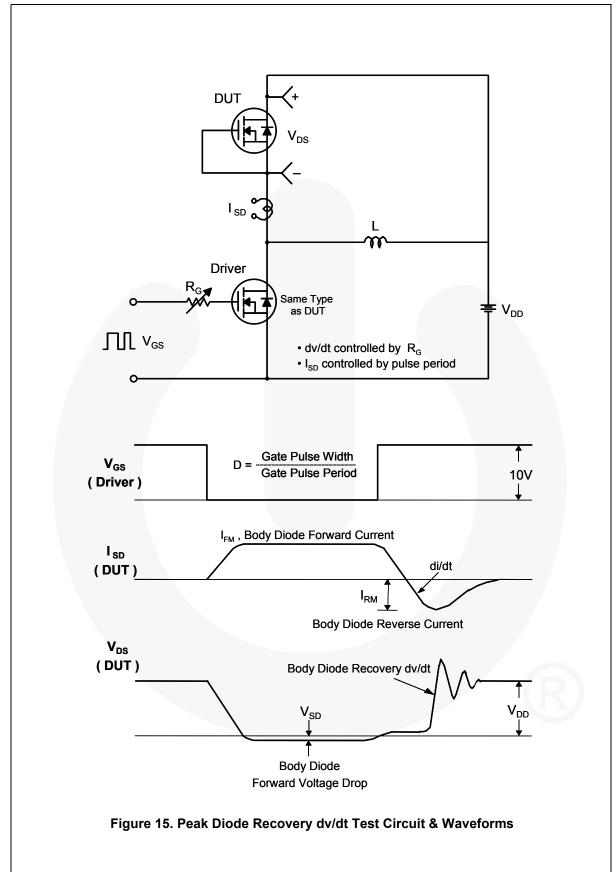
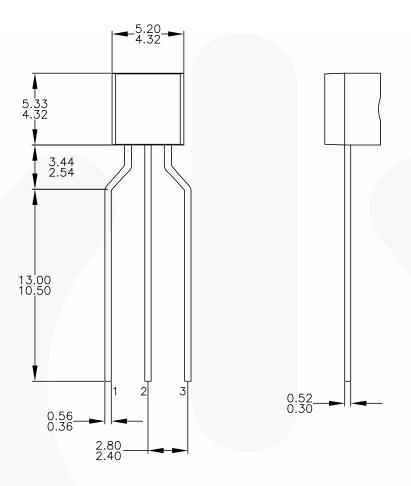
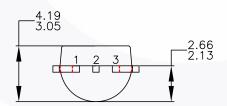


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions





NOTES: UNLESS OTHERWISE SPECIFIED

- DRAWING CONFORMS TO JEDEC MS-013,
- DRAWING CONFORMS 10 JEDEC MS-013, VARIATION AC.
 ALL DIMENSIONS ARE IN MILLIMETERS. DRAWING CONFORMS TO ASME Y14.5M-2009. DRAWING FILENAME: MKT-ZA03FREV3. FAIRCHILD SEMICONDUCTOR.

Figure 16. TO92, Molded, 3-Lead, 0.200 In Line Spacing LD Form (J61Z Option)

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